

- 26 -

**SEMICONDUCTOR DEVICES HAVING CONTACT PLUGS AND LOCAL
INTERCONNECTS AND METHODS FOR MAKING THE SAME**

Abstract

5 Provided is, for example, a method for the fabrication of electrical
interconnects in semiconductor devices wherein a substrate including two or more
transistors having gate regions wherein the gate regions are not exposed (e.g., the gate
regions are completely covered by an insulating cap) is provided. An insulating layer
overlying the transistors and the active areas is deposited, where upon a hard mask is created
10 and patterned to form a contact plug/interconnect opening over a first active area and a
portion of a first transistor immediately adjacent the first active area. A spacer is formed
within the contact plug/interconnect opening. Insulating material overlying active areas
between transistors is removed. A portion of the gate region of the first transistor is then
exposed and interconnect material is deposited within the contact plug/interconnect opening
15 onto the exposed portion of the gate region of the first transistor and the first active area.